## NSB1706DMW5T1G, NSVB1706DMW5T1G

## Dual Bias Resistor Transistor

## NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the NSB1706DMW5T1G, two BRT devices are housed in the SC–88A package which is ideal for low power surface mount applications where board space is at a premium.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

 $(T_A$  = 25°C unless otherwise noted, common for  $Q_1$  and  $Q_2)$ 

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current	Ι <sub>C</sub>	100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	PD	187 (Note 1) 256 (Note 2) 1.5 (Note 1) 2.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	670 (Note 1) 490 (Note 2)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Мах	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P <sub>D</sub>	250 (Note 1) 385 (Note 2) 2.0 (Note 1) 3.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	493 (Note 1) 325 (Note 2)	°C/W
Thermal Resistance, Junction-to-Lead	$R_{\theta JL}$	188 (Note 1) 208 (Note 2)	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

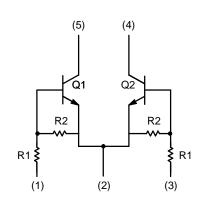
1. FR-4 @ Minimum Pad.

2. FR-4 @ 1.0 x 1.0 inch Pad.



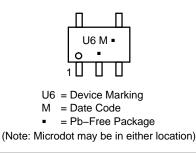
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#### MARKING DIAGRAM



#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NSB1706DMW5T1G	SC-88A (Pb-Free)	3000 / Tape & Reel
NSVB1706DMW5T1G	SC-88A (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### NSB1706DMW5T1G, NSVB1706DMW5T1G

ELECTRICAL CHARACTERISTICS (	T <sub>A</sub> = 25°C unless otherwise noted, comm	ion for $Q_1$ and $Q_2$ )
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Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	·		•		
Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	-	-	100	nAdc
Collector-Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0 \text{ V}, I_C = 0$ )	I <sub>EBO</sub>	_	-	0.18	mAdc
Collector-Base Breakdown Voltage $(I_C = 10 \ \mu A, I_E = 0)$	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 3) $(I_{C} = 2.0 \text{ mA}, I_{B} = 0)$	V <sub>(BR)</sub> CEO	50	-	-	Vdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain ( $V_{CE}$ = 10 V, I <sub>C</sub> = 5.0 mA)	h <sub>FE</sub>	80	200	-	
Collector-Emitter Saturation Voltage $(I_C = 10 \text{ mA}, I_B = 1 \text{ mA})$	V <sub>CE(sat)</sub>	-	-	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A})$	V <sub>i(off)</sub>	_	0.6	0.5	Vdc
Input Voltage (on) $(V_{CE} = 0.3 \text{ V}, I_C = 5 \text{ mA})$	V <sub>i(on)</sub>	1.3	0.9	-	Vdc
Output Voltage (on) $(V_{CC} = 5.0 \text{ V}, \text{ V}_{B} = 2.5 \text{ V}, \text{ R}_{L} = 1.0 \text{ k}\Omega)$	V <sub>OL</sub>	_	_	0.2	Vdc
Output Voltage (off) ( $V_{CC}$ = 5.0 V, $V_B$ = 0.25 V, $R_L$ = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R1/R2	0.055	0.1	0.185	

NOTE: New resistor combinations. Updated curves to follow in subsequent data sheets.

3. Pulse Test: Pulse Width < 300  $\mu$ s, Duty Cycle < 2.0%.

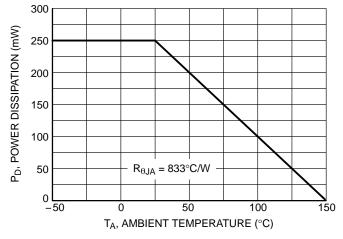


Figure 1. Derating Curve

# **NSEM**



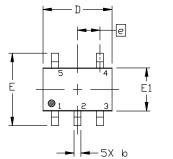
#### SC-88A (SC-70-5/SOT-353) CASE 419A-02 **ISSUE M**

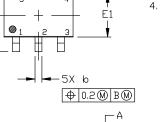
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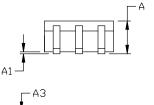
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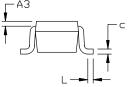
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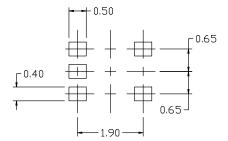
DATE 11 APR 2023











#### RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS			
MIU	MIN. NDM.		MAX,	
A	0.80	0.95	1.10	
A1	A1		0.10	
A3	0.20 REF			
b	0.10	0.20	0.30	
С	0.10		0.25	
D	1.80	2.00	5'50	
E	2.00	2.10	5'50	
E1	1.15	1.25	1.35	
e	0.65 BSC			
L	0.10	0.15	0.30	

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,

PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS,

OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

CONTROLLING DIMENSION: MILLIMETERS 419A-01 DBSOLETE, NEW STANDARD 419A-02

#### **GENERIC MARKING**





\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

Μ = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANOD 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4	E
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 1 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to style callout. If style to out in the datasheet r datasheet pinout or p	ype is not called efer to the device
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DESCRIPTION:	SC-88A (SC-70-	5/SOT-353)			PAGE 1 OF 1

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